# NPN Epitaxial Silicon Transistor

# **KSC2328A**

#### **Features**

- Audio Power Amplifier Application
- Complement to KSA928A
- 3 W Output Application

#### **ABSOLUTE MAXIMUM RATINGS**

(Values are at  $T_A = 25^{\circ}C$  unless otherwise noted.)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	2	Α
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

(Values are at  $T_A = 25^{\circ}C$  unless otherwise noted.) (Note 1)

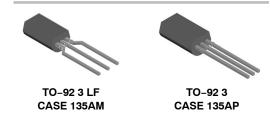
Symbol	Parameter	Value	Unit
$P_{D}$	Power Dissipation	1000	mW
	Derate Above 25°C	8.0	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	125	°C/W

<sup>1.</sup> PCB size: FR-4, 76 mm  $\times$  114 mm  $\times$  1.57 mm (3.0 inch  $\times$  4.5 inch  $\times$  0.062 inch) with minimum land pattern size.

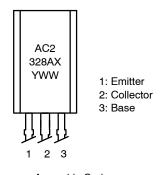


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#### **MARKING DIAGRAM**



A = Assembly Code C2328A = Device Code X = O / Y YWW = Date Code

## **ORDERING INFORMATION**

Device	Package	Shipping
KSC2328AOTA	TO-92 3 LF (Pb-Free)	2000 / Fan–Fold
KSC2328AYBU	TO-92 3 (Pb-Free)	6000 / Bulk Bag
KSC2328AYTA	TO-92 3 LF (Pb-Free)	2000 / Fan–Fold

### **KSC2328A**

## **ELECTRICAL CHARACTERISTICS**

(Values are at  $T_A = 25^{\circ}C$  unless otherwise noted.)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	30	-	-	V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0	30	-	-	V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1 mA, I <sub>C</sub> = 0	5	-	-	V
I <sub>CBO</sub>	Collector Cut-Off Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$	-	-	100	nA
I <sub>EBO</sub>	Emitter Cut-Off Current	V <sub>EB</sub> = 5 V, I <sub>C</sub> = 0	-	-	100	nA
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 500 mA	100	-	320	
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 500 mA	-	-	1.0	V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1.5 A, I <sub>B</sub> = 0.03 A	-	-	2.0	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 500 mA	-	120	-	MHz
C <sub>ob</sub>	Collector Output Capacitance	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz	-	30	_	pF

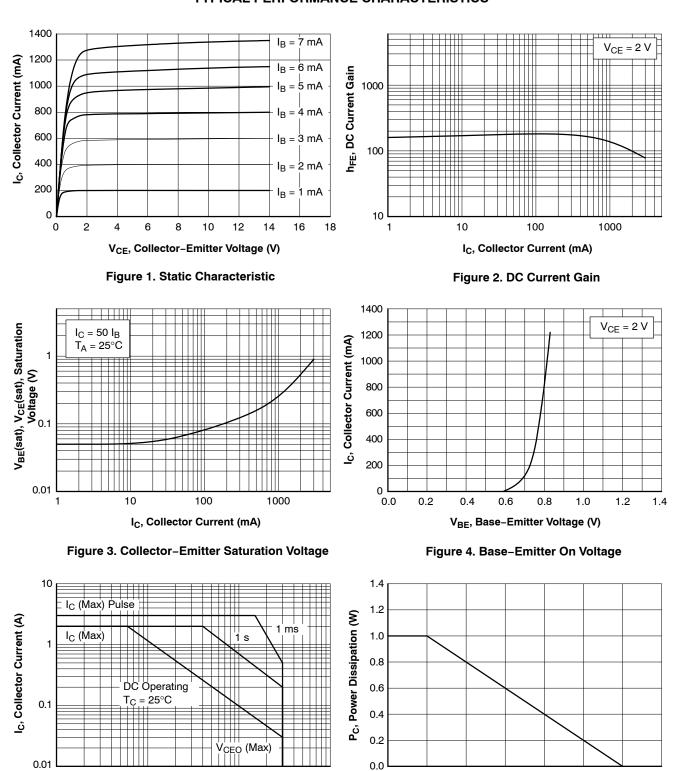
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## **h**FE CLASSIFICATION

Classification	0	Y
h <sub>FE</sub>	100 ~ 200	160 ~ 320

### KSC2328A

#### TYPICAL PERFORMANCE CHARACTERISTICS



100

V<sub>CE</sub>, Collector-Emitter Voltage (V) Figure 5. Safe Operating Area

0.1

25

50

75

100

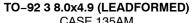
T<sub>A</sub>, Ambient Temperature (°C)

Figure 6. Power Derating

125

150

175



CASE 135AM ISSUE B

**DATE 14 JAN 2021** 



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- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, GATE REMAINS AND TIE BAR PROTRUSIONS.
- 4. DIMENSION & AND &2 DOES NOT INCLUDE DAMBAR PROTRUSION.
  DIMENSION &2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS		
DIM	MIN.	N□M.	MAX.
Α	3.70	3.90	4.10
A1	1.25	1.45	1.65
b	0.35	0.50	0.60
b2	0.62		0.78
С	0.35	0.45	0.55
D	7.80	8.00	8.20
Ε	4.70	4.90	5.10
E2	3.70	3.90	4.10
е	1.27 BSC		
e2	2.50 BSC		
F		2.45 REF	
L		13.00 REF	
L2	1.50		1.90
L3	2.60		3,40
L4	10.40 REF		

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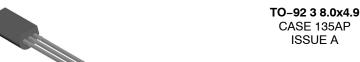
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	MILLIMETERS		
DIM	MIN.	N□M.	MAX.
Α	3.70	3.90	4.10
A1	1.25	1.45	1.65
Ø	0.40	0.50	0.60
b2	0.62		0.78
U	0.35	0.45	0.55
D	7.80	8.00	8.20
Е	4.70	4.90	5.10
E2	3.70	3.90	4.10
е		1.27 BSC	
F		2.45 REF	
Г	13.30		14.20
L2		1.70 REF	

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